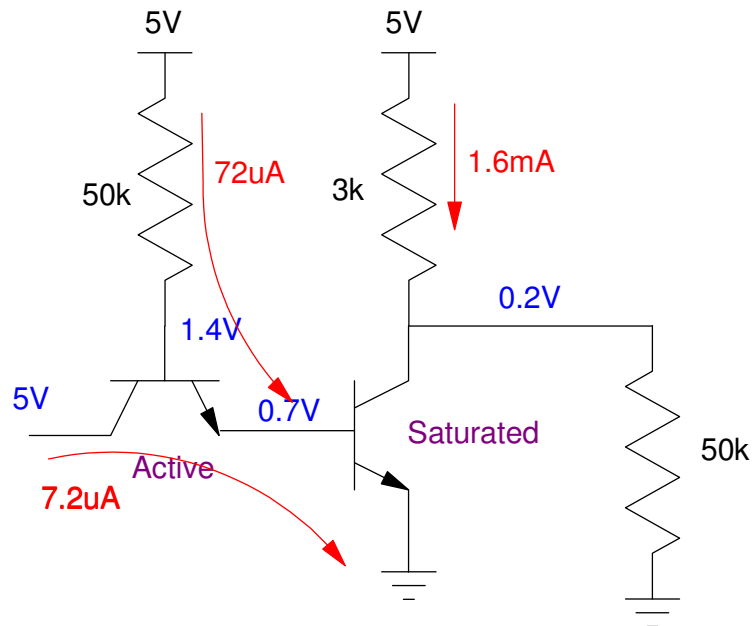
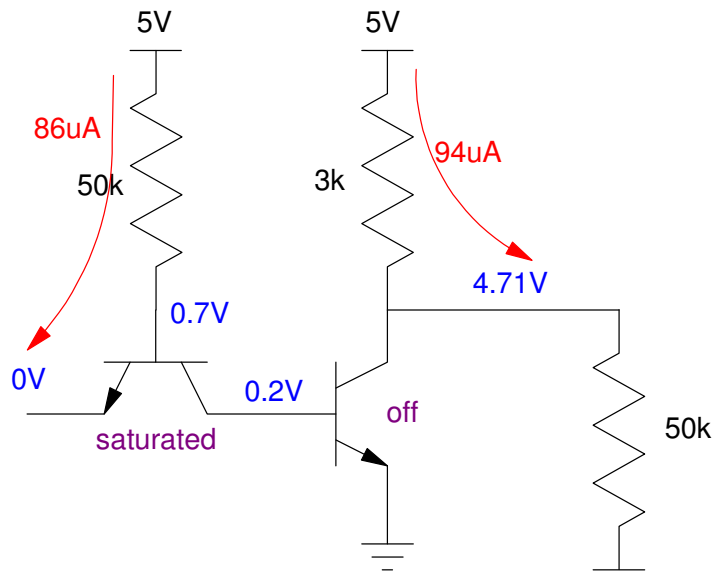


ECE 320 - Homework #9

TTL Logic, MOSFET Theory, MOSFET Switches. Due Monday, March 19th

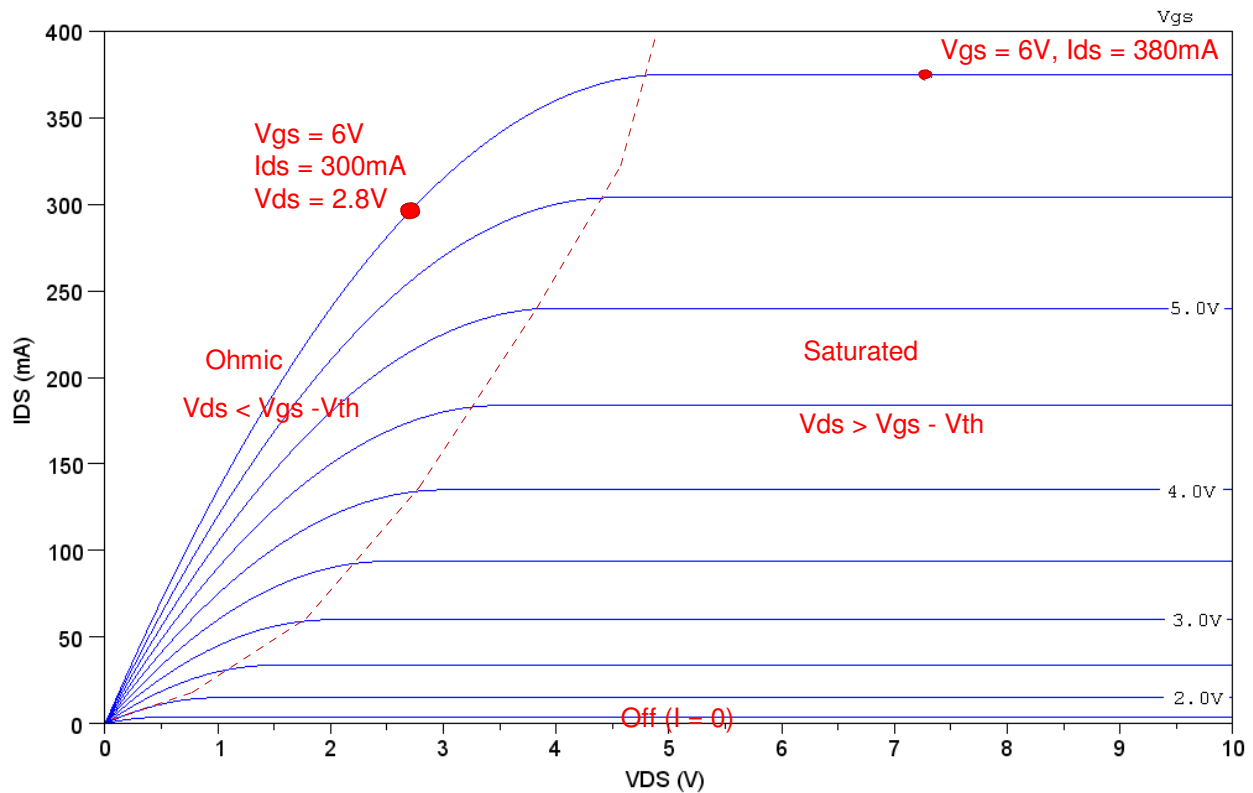
TTL Logic:

1) Determine the voltages and currents for the following TTL AND gate. Assume ideal silicon diodes and transistors with $\beta = 100$.



MOSFET:

2a) Label the Off / Saturated / Ohmic regions for the following n-channel MOSFET



2b) Determine the transconductance gain, k_n ($V_{th} = 1.0V$)

Pick a point in the Ohmic region

Pick a point in the saturated region

$$I_{ds} = k_n \left(V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$I_{ds} = \frac{k_n}{2} (V_{gs} - V_{th})^2$$

$$300mA = k_n \left(6V - 1V - \frac{2.8V}{2} \right) 2.8V$$

$$380mA = \frac{k_n}{2} (6V - 1V)^2$$

$$k_n = 0.0297 \frac{A}{V^2}$$

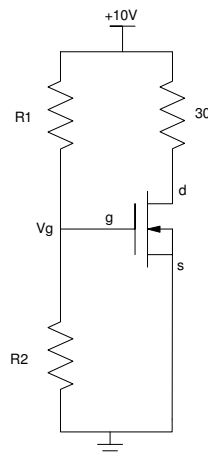
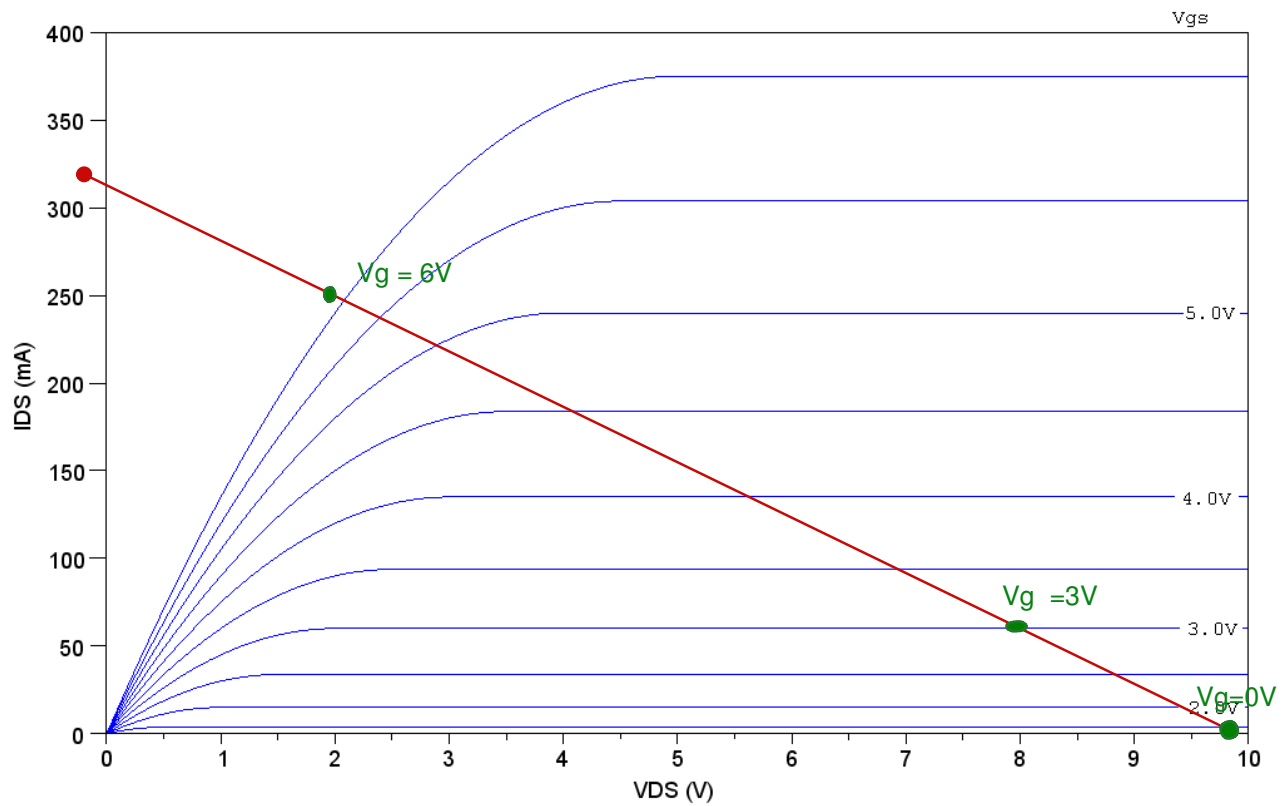
$$k_n = 0.0304 \frac{A}{V^2}$$

You can use a point in either region to find k_n . You just have to use the appropriate equation for that region.

3a) Draw the load line for the following circuit on the previous graph

3b) Determine the Q-point (V_{ds} , I_{ds}) when

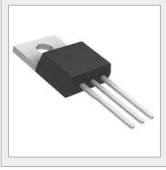
- $V_g = 0V$ $V_{ds} = 10V$, $I_{ds} = 0mA$ (off)
- $V_g = 3V$ $V_{ds} = 8.2V$, $I_{ds} = 62mA$ (saturated)
- $V_g = 6V$ $V_{ds} = 2V$, $I_{ds} = 250mA$ (Ohmic)



Assume a AOT2618L n-channel MOSFET:

- 23A max continuous current I_{ds}
- 70A max pulse current
- 19 mOhm @ 20A @ $V_{gs} = 10V$
- $V_{th} = 2.5V$ (max)
- \$0.72 (qty = 100)
- Digikey part number: 785-1438-5-ND

[Product Index](#) > [Discrete Semiconductor Products](#) > [Transistors - FETs, MOSFETs - Single](#) > Alpha & Omega Semiconductor Inc. AOT2618L



Product Overview	
Digi-Key Part Number	785-1438-5-ND
Quantity Available	1,517 Can ship immediately
Manufacturer	Alpha & Omega Semiconductor Inc.
Manufacturer Part Number	AOT2618L
Description	MOSFET N-CH 60V 7A TO220
Lead Free Status / RoHS Status	Lead free / RoHS Compliant
Moisture Sensitivity Level (MSL)	1 (Unlimited)
Manufacturer Standard Lead Time	20 Weeks
Detailed Description	N-Channel 60V 7A (Ta), 23A (Tc) 2.1W (Ta), 41.5W (Tc) Through Hole TO-220

Price & Procurement		
Quantity	1	
785-1438-5-ND		
Customer Reference		
Add to Cart		
All prices are in USD.		
Price Break	Unit Price	Extended Price
1	1.04000	\$1.04
10	0.92100	\$9.21
100	0.72770	\$72.77
500	0.56430	\$282.15
1,000	0.44550	\$445.50

Submit a [request for quotation](#) on quantities greater than those displayed.

[Documents & Media](#)

4) Determine the transconductance gain, k_n

The spec (19mOhm) refers to the Ohmic region

$$V_{ds} = 0.019\Omega \cdot 20A = 0.38V$$

$$I_{ds} = k_n \left(V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$20A = k_n \left(10V - 2.5V - \frac{0.38V}{2} \right) 0.38V$$

$$k_n = 7.20 \frac{A}{V^2}$$

5) Determine the voltages for the MOSFET circuit to the right

Assume Ohmic region

$$(V_{ds} < V_{gs} - V_{th} = 2.5V)$$

To solve for V_{ds} and I_{ds} you need two equations to solve for two unknowns:

$$a) \quad I_{ds} = k_n \left(V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$I_{ds} = 7.2 \left(5 - 2.5 - \frac{V_{ds}}{2} \right) V_{ds}$$

$$b) \quad V_{ds} + 10I_{ds} + 5.7 = 10$$

Solving gives two solutions:

$$V_{ds} = 0.02387V \quad I_{ds} = 427.6mA$$

$$V_{ds} = 5.004V \quad I_{ds} = -70.39mA$$

The solution close to $V_{ds} = 0$ is correct

Answer:

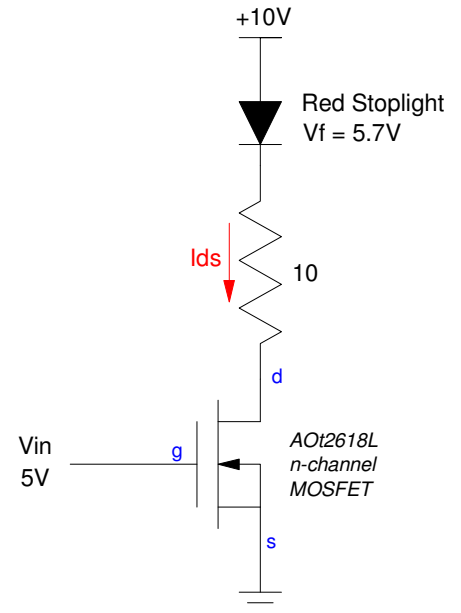
$$V_{ds} = 0.02387V \quad I_{ds} = 427.6mA$$

Note: The actual resistance is

$$R_{ds} = \frac{V_{ds}}{I_{ds}} = 55.8m\Omega$$

If you assume $R_{ds} = 19m\Omega$, your answer will be slightly off:

$$V_{ds} = 0.02396V \quad I_{ds} = 427.6mA$$



6) Modify this circuit so that $I_{ds} = 1\text{A}$ when $V_{in} = 5\text{V}$.

Assume the on resistance is 19m Ohms. For 1A

$$R_{total} = \left(\frac{4.3\text{V}}{1\text{A}} \right) = 4.3\Omega$$

$$R_{total} = R_{ds} + R_d$$

$$4.3\Omega = 0.019\Omega + R_d$$

$$R_d = 4.281\Omega$$

or roughly 4.3 Ohms

This gives an answer that is slightly off. Solving two equations for two unknowns:

$$I_{ds} = k_n \left(V_{gs} - V_{th} - \frac{V_{ds}}{2} \right) V_{ds}$$

$$V_{ds} + 4.3I_{ds} + 5.7 = 10$$

Solving...

$$V_{ds} = 0.05545\text{ V}$$

$$I_{ds} = 987.1\text{ mA}$$

meaning that

$$R_{ds} = 0.056\text{ Ohms}$$

(vs 0.019 Ohms assumed)